Amplifier Transistors NPN Silicon

COLLECTOR 1 BASE 3 EMITTER

MAXIMUM RATINGS

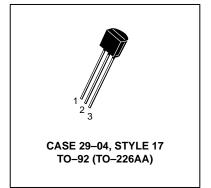
Rating	Symbol	BC 182	BC 183	BC 184	Unit	
Collector-Emitter Voltage	VCEO	50	30	30	Vdc	
Collector-Base Voltage	Vсво	60	45	45	Vdc	
Emitter-Base Voltage	VEBO	6.0			Vdc	
Collector Current — Continuous	lC	100			mAdc	
Total Device Dissipation @ T _A = 25°C Derate above 25°C	PD	350 2.8			mW mW/°C	
Total Device Dissipation @ T _C = 25°C Derate above 25°C	PD	1.0 8.0		Watts mW/°C		
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150			°C	

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	357	°C/W
Thermal Resistance, Junction to Case	$R_{ heta JC}$	125	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit	
OFF CHARACTERISTICS							
Collector-Emitter Breakdown Voltage (I _C = 2.0 mA, I _B = 0)	BC182 BC183 BC184	V(BR)CEO	50 30 30	_ _ _	_ _ _	V	
Collector-Base Breakdown Voltage (I _C = 10 μA, I _E = 0)	BC182 BC183 BC184	V(BR)CBO	60 45 45	_ _ _ _	_ _ _	V	
Emitter-Base Breakdown Voltage (I _E = 100 μA, I _C = 0)		V(BR)EBO	6.0	_	_	V	
Collector Cutoff Current (V _{CB} = 50 V, V _{BE} = 0) (V _{CB} = 30 V, V _{BE} = 0)	BC182 BC183 BC184	ICBO	_ _ _	0.2 0.2 0.2	15 15 15	nA	
Emitter–Base Leakage Current (V _{EB} = 4.0 V, I _C = 0)		IEBO	_	_	15	nA	



BC182,A,B BC183 BC184

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted) (Continued)

Characteristic		Symbol	Min	Тур	Max	Unit
ON CHARACTERISTICS						
DC Current Gain (I _C = 10 μ A, V _{CE} = 5.0 V)	BC182 BC183 BC184	hFE	40 40 100	_ _ _	_ _ _	_
$(I_C = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V})$	BC182 BC183 BC184		120 120 250	_ _ _	500 800 800	
$(I_C = 100 \text{ mA}, V_{CE} = 5.0 \text{ V})$	BC182 BC183 BC184		80 80 130	_ _ _	_ _ _	
Collector-Emitter On Voltage ($I_C = 10 \text{ mA}, I_B = 0.5 \text{ mA}$) ($I_C = 100 \text{ mA}, I_B = 5.0 \text{ mA}$)(1)		VCE(sat)	_ _ _	0.07 0.2	0.25 0.6	V
Base-Emitter Saturation Voltage (IC = 100 mA, I _B = 5.0 mA) ⁽¹⁾		V _{BE(sat)}	_	_	1.2	V
Base–Emitter On Voltage (I _C = 100 μA, V _{CE} = 5.0 V) (I _C = 2.0 mA, V _{CE} = 5.0 V) (I _C = 100 mA, V _{CE} = 5.0 V)(1)		VBE(on)	— 0.55 —	0.5 0.62 0.83	 0.7 	V
DYNAMIC CHARACTERISTICS		•			•	
Current-Gain — Bandwidth Product (I _C = 0.5 mA, V _{CE} = 3.0 V, f = 100 MHz)	BC182 BC183 BC184	fΤ	_ _ _	100 120 140	_ _ _	MHz
$(I_C = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}, f = 100 \text{ MHz})$	BC182 BC183 BC184		150 150 150	200 240 280	_ _ _	
Common Base Output Capacitance (V _{CB} = 10 V, I _C = 0, f = 1.0 MHz)		C _{ob}	_	_	5.0	pF
Common Base Input Capacitance ($V_{EB} = 0.5 \text{ V}$, $I_{C} = 0$, $f = 1.0 \text{ MHz}$)		C _{ib}	_	8.0	_	pF
Small–Signal Current Gain (I _C = 2.0 mA, V _{CE} = 5.0 V, f = 1.0 kHz)	BC182 BC183 BC184 BC182A BC182B	h _{fe}	125 125 240 125 240	_ _ _ _	500 900 900 260 500	_
Noise Figure (IC = 0.2 mA, VCE = 5.0 V, RS = 2.0 k Ω , f = 1.0 kHz) (IC = 0.2 mA, VCE = 5.0 V, RS = 2.0 k Ω , f = 1.0 kHz, f = 200 Hz)	BC184 BC182 BC183 BC184	NF	1111	2.0 2.0 2.0 2.0	4.0 10 10 4.0	dB

^{1.} Pulse Test: Tp 300 s, Duty Cycle 2.0%.

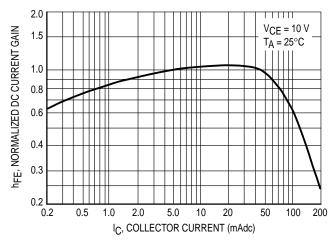


Figure 1. Normalized DC Current Gain

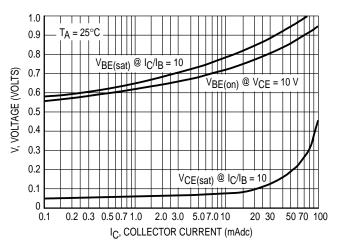


Figure 2. "Saturation" and "On" Voltages

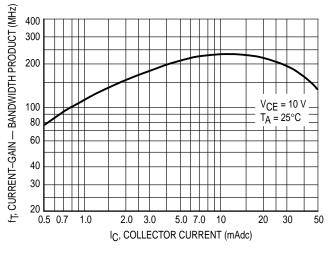


Figure 3. Current-Gain — Bandwidth Product

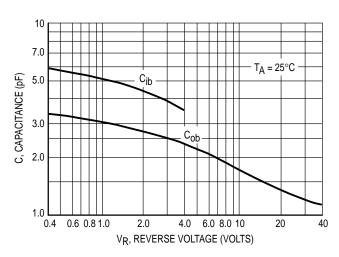


Figure 4. Capacitances

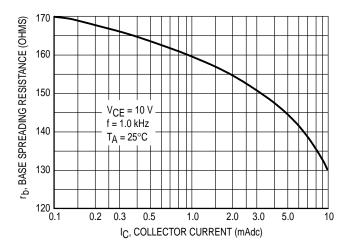
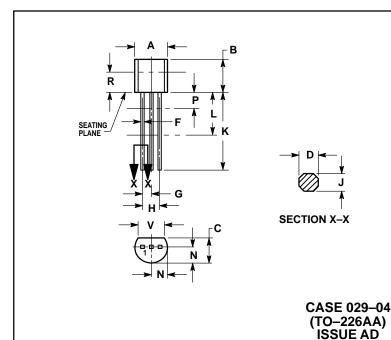


Figure 5. Base Spreading Resistance

PACKAGE DIMENSIONS



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
 CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
- DIMENSION F APPLIES BETWEEN P AND L. DIMENSION F APPLIES BETWEEN F AIND L.
 DIMENSION D AND J APPLY BETWEEN L AND K
 MINIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.175	0.205	4.45	5.20	
В	0.170	0.210	4.32	5.33	
С	0.125	0.165	3.18	4.19	
D	0.016	0.022	0.41	0.55	
F	0.016	0.019	0.41	0.48	
G	0.045	0.055	1.15	1.39	
Н	0.095	0.105	2.42	2.66	
J	0.015	0.020	0.39	0.50	
K	0.500		12.70		
L	0.250		6.35		
N	0.080	0.105	2.04	2.66	
Р		0.100	_	2.54	
R	0.115		2.93		
V	0.135		3 43		

STYLE 17:

PIN 1. COLLECTOR

2. BASE

3. EMITTER

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